

RECEIVED

TC 1700

14 1765

PATENT

IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

In Re U.S. Pat	ent Application) Art Unit: 1765				
Applicant(s):	NAKAMURA et al.)				
Serial No.:	09/856,212) I hereby certify that this) correspondence is being deposited				
Filed:	May 18, 2001) with the United Postal Service as) first class mail in an envelope				
For:	PRODUCTION METHOD FOR SILICON SINGLE CRYSTAL AND PRODUCTION DEVICE FOR SINGLE CRYSTAL INGOT, AND HEAT TREATING METHOD FOR SILICON SINGLE CRYSTAL WAFFR	 addressed to: MAIL STOP DD / Commissioner for Patents / PO Box 1450 / Alexandria, Virginia 22313- 1450, on June 23, 2003. Gerald T. Shekleton Reg. No. 27,466 				

SUPPLEMENTAL INFORMATION DISCLOSURE STATEMENT

MAIL STOP DD Commissioner for Patents P.O. Box 1450 Alexandria, Virginia 22313-1450

Sir:

Pursuant to 37 C.F.R. §1.97, a list of documents is disclosed on the attached Form PTO-1449 that may be material to the examination of this application. The listed Documents are enclosed herewith.

No inferences should be drawn that the attached list represents a comprehensive investigation, or that any material disclosed is equivalent to the subject invention. In addition, none of the documents that have publication dates prior to the priority date of the above application anticipate the invention in this application.

The cited document(s) disclose numerous specific features. There has been no attempt to

Serial No. 09/856,212

list each and every feature disclosed by each document. The Examiner is requested to review the

document(s) and determine the extent of the materiality of the document disclosures with respect to

the present invention.

The discussion of any art and the citation of any document(s) herein is not to be construed

as an admission that the art or document disclosure is necessarily within the invention field of

endeavor, that the art or document disclosure is necessarily prior in time to a particular date which

may be relevant to the instant patent application, and/or that the art or document disclosure is

otherwise necessarily prior art as defined by the patent law with respect to the instant invention and

application.

Also, there is reserved the right to later set forth how the instant invention is distinguished

over the disclosure of any document or other art, including the disclosures of the art and

document(s) recited herein, that may be cited by the Examiner in rejecting a claim in the instant

patent application. The recitation herein of the art and document(s) is not to be construed as an

assertion that more pertinent art could not possibly be in existence.

Respectfully submitted,

WELSH & KATZ, LTD.

Gerald T. Shekleton

Registration No. 27,466

Dated: <u>June 23, 2003</u>

Welsh & Katz, Ltd.

120 South Riverside Plaza, 22nd Floor

Chicago, Illinois 60606

Telephone: 312/655-1500



RECEIVED JUN 2 7 2003

TC 1700

Sheet $\perp \!\!\! \perp$ of $\perp \!\!\! \perp$

(Rev. 5/92)	U.S. Department of Commerce Patent and Trademark Office		Atty. Docket No.		Serial No.					
Comparable to Form PTO-1449		Patent and Trade	emark Office	82821		09/856,212				
INFORMATION DISCLOSURE CITATION										
(Use several sheets if necessary)										
			Applicant NAKAMURA et al.							
			Filing Date May 18, 2001		Group 1765					
• •			U.S. PATEN	T DOCUMENTS						
*Examiner						Filing Date		g Date		
Initial	Document Number	Date	Name		Class	Subclass	If Appropriate			
	4,437,922	03/20/1984	Bischoff et al.							
	4,944,834	07/31/1990	Tada et al.							
	6,036,776	03/14/2000	Kotooka et a	ıl.						
•		F	OREIGN PAT	ENT DOCUMENTS						
						Translation				
	Document Number	Date	Name of Patentee		Class	Subclass	Yes	No		
			MEMCEL		Class	Subclass		<u> </u>		
	EP 0823497	02/11/1998	MEMC Electronic Materials, Inc.							
	EP 0866150	09/23/1998	Wacker Siltronic Gesellschaft fur					1		
	EP 0785298	06/26/2002	MEMC Electronic Materials, Inc.				,			
	JP 03-279290	12/10/1991	Osaka Titanium Co., Ltd.					1		
	JP 05-194076	08/03/1993	Komatsu Denshi Kinzoku KK			ļ		-		
	JP 07-133187	05/23/1995	Komatsu Electron Metals Co., Ltd.				. <u> </u>			
	WO 98/45507	10/15/1998	MEMC Electronic Materials, Inc.							
	WO 98/45508	10/15/1998	MEMC Elec	tronic Materials, Inc.		<u> </u>				
	ОТН	ER DOCUMEN	TS (Including	Author, Title, Date, Pertinent Page	s, Etc.)					
		NAKAMURA, KOZO et al.: "Formation process of grown-in defects in Czochralski grown silicon crystals" JOURNAL OF CRYSTAL GROWTH 180 (1997) 61-72								
	j.	AMMON, WILFRIED VON et al.: "The dependence of bulk defects on the axial temperature gradient of silicon crystals during Czochralski growth" 2300 JOURNAL OF CRYSTAL GROWTH 151 (1995) June I, Nos. 3/4, Amersterdam, NL, Pages 273-277								
Examiner				Date Considered						
*Examiner:	Initial if citation considered,			nformance with MPEP 609; draw	line through	citation if not in	conformanc	e and not		